

COMPARISON TABLE

FOR POWER MEASUREMENTS

MODEL	P _{MAX}	NOISE LEVEL	λ _{MIN}	λ _{MAX}	SENSOR TYPE	APERTURE	SEE PAGE
PH5B-Ge	40 μW	40 pW	800 nm	1.65 μm	Germanium	5 mm Ø	110
PH10B-Si	200 μW	50 pW	210 nm	1.08 μm	UV-Silicon	10 mm Ø	110
PH100-SiUV	4 mW	10 pW	210 nm	1.08 μm	UV-Silicon	10 mm Ø	112
PH100-SiUV-OD.3	11 mW	30 pW	210 nm	1.08 μm	UV-Silicon	10 mm Ø	112
PH100-SiUV-OD1	38 mW	100 pW	400 nm	1.08 μm	UV-Silicon	10 mm Ø	112
PH20-Ge	30 mW	60 pW	800 nm	1.65 μm	Germanium	5 mm Ø	112
PH100-Si-HA	36 mW	10 pW	350 nm	1.08 μm	Silicon	10 mm Ø	112
PH100-Si-HA-OD1	300 mW	100 pW	420 nm	1.08 μm	Silicon	10 mm Ø	112
PH20-Ge-OD1	300 mW	600 pW	900 nm	1.65 μm	Germanium	5 mm Ø	112
PRONTO-Si	300 mW	10 pW	320 nm	1.1 μm	Silicon	10 X 10 mm	116
PH20-Ge-OD2	500 mW	6 nW	950 nm	1.65 μm	Germanium	5 mm Ø	105
PH100-Si-HA-OD2	750 mW	1 nW	630 nm	1.1 μm	Silicon	10 mm Ø	112

FOR ENERGY MEASUREMENTS

MODEL	E _{MAX}	NOISE LEVEL	λ _{MIN}	λ _{MAX}	SENSOR TYPE	APERTURE	SEE PAGE
PE3B-Si	30 pJ	8 fJ	210 nm	1.08 μm	UV-Silicon	3 mm Ø	114
PE3B-In	300 pJ	30 fJ	900 nm	1.7 μm	InGaAs	3 mm Ø	114
PE5B-Ge	3 nJ	1 pJ	800 nm	1.65 μm	Germanium	5 mm Ø	114
PE10B-Si	150 nJ	1.5 pJ	210 nm	1.08 μm	UV-Silicon	10 mm Ø	114

 Available with INTEGRA all-in-one detector + meter

